



SANYO Semiconductors

## DATA SHEET

# 2SK3094 — N-Channel Silicon MOSFET

## General-Purpose Switching Device Applications

### Features

- High-speed switching.
- Low ON-resistance.
- 15V drive.

### Specifications

#### Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V <sub>DSS</sub>		400	V
Gate-to-Source Voltage	V <sub>GSS</sub>		±30	V
Drain Current (DC)	I <sub>D</sub>		5.5	A
Drain Current (Pulse)	I <sub>DP</sub>		22	A
Allowable Power Dissipation	P <sub>D</sub>	T <sub>c</sub> =25°C	55	W
Channel Temperature	T <sub>ch</sub>		150	°C
Storage Temperature	T <sub>stg</sub>		-55 to +150	°C

#### Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	V(BR) <sub>DSS</sub>	I <sub>D</sub> =1mA, V <sub>GS</sub> =0V	400			V
Zero-Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =320V, V <sub>GS</sub> =0V			1.0	mA
Gate-to-Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> = ±30V, V <sub>DS</sub> =0V			±100	nA
Cutoff Voltage	V <sub>GS(off)</sub>	V <sub>DS</sub> =10V, I <sub>D</sub> =1mA	3.0		4.0	V
Forward Transfer Admittance	y <sub>fs</sub>	V <sub>DS</sub> =10V, I <sub>D</sub> =2.8A	1.3	2.6		S
Static Drain-to-Source On-State Resistance	R <sub>DS(on)</sub>	I <sub>D</sub> =2.8A, V <sub>GS</sub> =15V		0.92	1.2	Ω
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =20V, f=1MHz		660		pF
Output Capacitance	C <sub>oss</sub>	V <sub>DS</sub> =20V, f=1MHz		170		pF
Reverse Transfer Capacitance	C <sub>rss</sub>	V <sub>DS</sub> =20V, f=1MHz		80		pF

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SANYO Semiconductor Co., Ltd.

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# 2SK3094

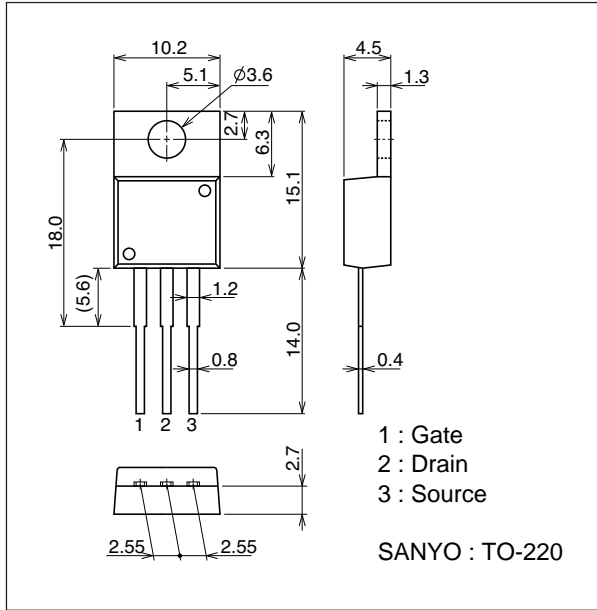
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Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Total Gate Charge	Qg	V <sub>DS</sub> =200V, I <sub>D</sub> =5.5A, V <sub>GS</sub> =10V		20		nC
Turn-ON Delay Time	t <sub>d(on)</sub>	See specified Test Circuit.		14		ns
Rise Time	t <sub>r</sub>	See specified Test Circuit.		15		ns
Turn-OFF Delay Time	t <sub>d(off)</sub>	See specified Test Circuit.		45		ns
Fall Time	t <sub>f</sub>	See specified Test Circuit.		25		ns
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> =5.5A, V <sub>GS</sub> =0V			1.2	V

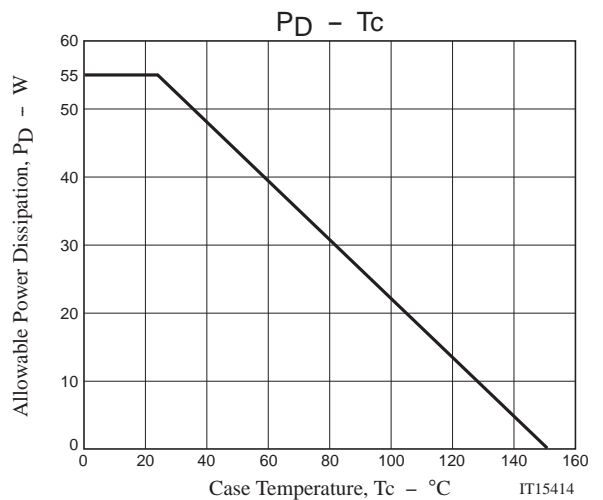
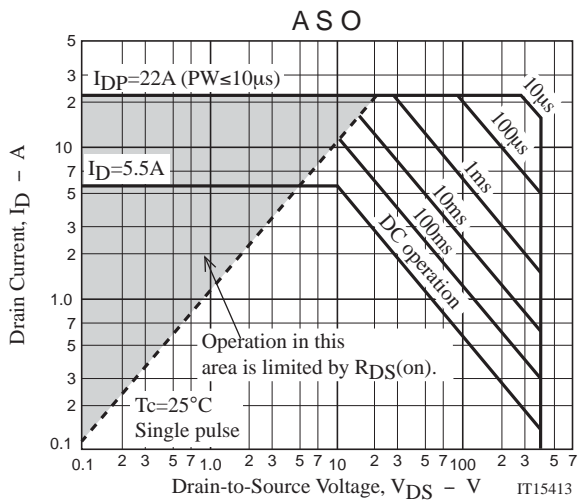
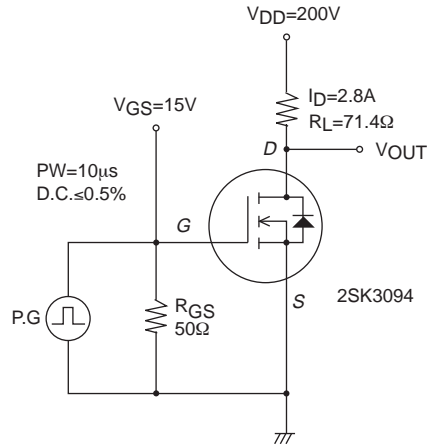
## Package Dimensions

unit : mm (typ)

7507-002



## Switching Time Test Circuit



Note on usage : Since the 2SK3094 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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